

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

Claims 1-16 (Canceled)

Claim 17 (Previously Presented): A semiconductor device comprising:

a first semiconductor layer and a second semiconductor layer over an insulating surface;

a first insulating film over the first semiconductor layer and over the second semiconductor layer;

a first electrode over the first insulating film, said first electrode overlapping the first semiconductor layer;

a second electrode over the first insulating film, said second electrode overlapping the second semiconductor layer;

a source wiring over the first insulating film;

a second insulating film covering the first electrode and the source wiring;

a gate wiring over the second insulating film, said gate wiring connected to the first electrode;

a connection electrode over the second insulating film, said connection electrode connected to the source wiring and the first semiconductor layer; and

a pixel electrode over the second insulating film, said pixel electrode connected to the first semiconductor layer;

wherein the pixel electrode overlays the source wiring with the second insulating film interposed therebetween.

Claim 18 (Previously Presented): A device according to claim 17, wherein the first electrode is a gate electrode.

Claim 19 (Previously Presented): A device according to claim 17, wherein a storage capacitor is formed by the second semiconductor layer, the second electrode, and the first insulating film.

Claim 20 (Previously Presented): A device according to claim 17, wherein:
the first semiconductor layer contains an impurity element which imparts one conductivity into the semiconductor; and
the second semiconductor layer contains an impurity element which imparts one conductivity, opposite to that contained in the first semiconductor layer, into the semiconductor.

Claim 21 (Previously Presented): A device according to claim 17, wherein the gate wiring comprising an element selected from the group consisting of polysilicon doped with an impurity element which imparts one conductivity; W; WSix; Al; Cu; Ta; Cr; and Mo as its main constituent, and a lamination film of the elements.

Claim 22 (Previously Presented): A device according to claim 17, wherein the second insulating film is composed of a first insulating layer having silicon as its main constituent, and a second insulating layer comprising an organic resin material.

Claim 23 (Previously Presented): A device according to claim 17, wherein the semiconductor device is a reflecting type liquid crystal display device.

Claim 24 (Previously Presented) A device according to claim 17, wherein the semiconductor device is a device selected from the group consisting of a personal computer, a

video camera, a portable information terminal, a digital camera, a digital video disk player, and an electronic amusement device.

Claims 25-75 (Canceled)

Claim 76 (Previously Presented): A device according to claim 17, wherein said first insulating film is a gate insulating film.

Claim 77 (Previously Presented): A device according to claim 17, wherein the first electrode and the source wiring comprise the same material and are formed by the same process.

Claim 78 (Canceled)

Claim 79 (New): A device according to claim 17, wherein the second electrode is a capacitor electrode.